

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	102	shigeno.in. and (liquid adj crystal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 10:49
L15	9	14 and ito and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 10:49
L16	2958	((liquid near2 crystal) lcd) and substrate and ((thin near2 film) transistor tft) and (pixel near2 electrode) and ((non-oxidiz\$4 near3 (metal film layer coat)) or (chromium tunsten)) and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:09
L17	63	((((liquid near2 crystal) lcd) and substrate and ((thin near2 film) transistor tft) and (pixel near2 electrode) and ((non-oxidiz\$4 near3 (metal film layer coat)) or (chromium tunsten)) and hole).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:13
L18	18	((((liquid near2 crystal) lcd) and substrate and ((thin near2 film) transistor tft) and ((second or reflective) near2 pixel near2 electrode) and ((non-oxidiz\$4 near3 (metal film layer coat)) or (chromium tunsten)) and hole and passivation and gate and source and drain).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L19	1790	349/113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L20	665	349/114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L21	1555	349/42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L22	273	349/41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17

L23	1822	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L24	4591	19 20 21 22 23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
L25	22	24 and 17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 11:17
S1	367009	((liquid near3 crystal near3 display) or lcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:00
S2	128773	S1 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:00
S3	1965688	substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:00
S4	77136	(thin near3 film near3 transistor) or tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:01
S5	11854	(pixel near3 electrode) near8 (transparent or ito or izo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:01
S6	40414	passivation near3 (film or layer or coat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:02
S7	2892	S1 and S3 and S4 and S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:06

S8	2739	S7 and gate and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:07
S9	2368	S8 and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:41
S10	4	S9 and (non\$1oxidiz\$3 near3 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:07
S11	681	S9 and (reflect\$3 near3 (layer or film or electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:41
S12	1574	349/113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:42
S13	518	349/114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 14:42
S14	108	S11 and (S12 or S13)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:03
S15	61	S14 and (cr or chromium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 15:04